L Number	Hits	Search Text	DB	Time stamp
27	1701	((semiconducting or semiconductor) near3 group near3 IV)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:13
28	601	((semiconducting or semiconductor) near3 group near3 IV) and ((substrate or surface) near5 (orientation or direction))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:14
29	107	((semiconducting or semiconductor) near3 group near3 IV).ti,ab,clm. and ((substrate or surface) near5 (orientation or direction))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:14
30	44	((semiconducting or semiconductor) near3 group near3 IV).ti,ab,clm. and ((substrate or surface) near5 (orientation or direction)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:14
31	2	((semiconducting or semiconductor) near3 group near3 IV) and ((substrate or surface) near5 (orientation or direction)) and (pfet or (p near fet))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:16
32	99	((semiconducting or semiconductor) near3 group near3 IV) and ((substrate or surface) near5 (orientation or direction)) and (current near (flow or flowing or direction or orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:16
33	8	substrate same (orientation or direction) same current same (flow or flowing) same (pfet or nfet or (p near fet) or (n near fet))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:18
34	235	substrate same (orientation or direction) same current same (flow or flowing) same (pfet or nfet or (p near2 fet) or (n near2 fet) or mosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:19
35	0	substrate same (orientation or direction) same current same (flow or flowing) same (pfet or nfet or (p near2 fet) or (n near2 fet) or mosfet) same gate same (insulating or dielectric) same spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:19
36	0	(substrate same (orientation or direction) same current same (flow or flowing) same (pfet or nfet or (p near2 fet) or (n near2 fet) or mosfet)).clm. and gate.clm. and (insulating or dielectric).clm. and spacer.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:20

| 37 | 1 | (substrate same (orientation or direction) same current same (flow or flowing) same (pfet or nfet or (p near2 fet) or (n near2 fet) or mosfet)).clm. and gate.clm. and (insulating or dielectric).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/10/29 17:20 |